

r vo pehosilion Frocess For Enhanced Properties Of Metal Films* Michael Rumer et al.

Appln. No.: 09/675,627



2/3

Ti <0002> Grain Performanc vs. H₂ Amount Introduced in Ti Module During Burst Step

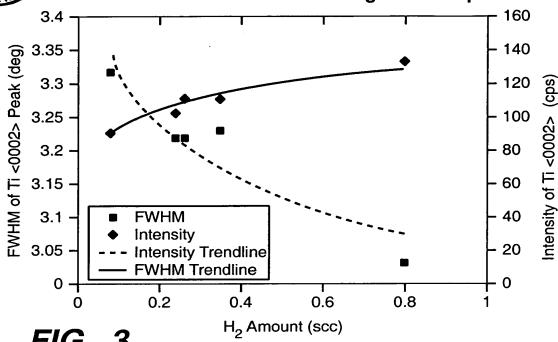


FIG._3

TiN <111> and AI <111> Grain Performance vs. H₂ Amount Introduced in Ti Module During Burst Step

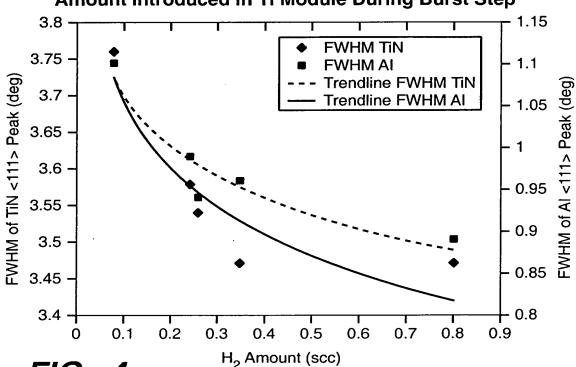


FIG._4



3/3

FWHM of AI <111> P ak vs. Thickness of Ti Underlayer

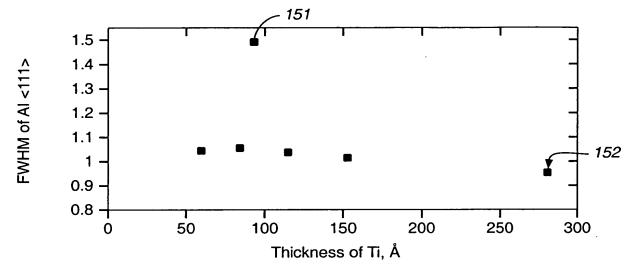


FIG._5a

Intensity of AI <111> Peak vs. Thickness of Ti Underlayer

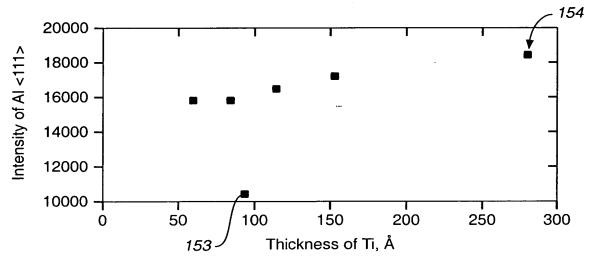


FIG._5b